## NSN 5962-01-145-8946

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Operating Tempurature Range:
-55.0/+125.0 degrees celsius
End Application:
Aim-54c guided missile
Features Provided:
Monolithic and burn in and programmable
Inclosure Material:
Metal or ceramic or plastic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Time Rating Per Chacteristic:
90.00 nanoseconds propagation delay time, low to high level output and 90.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Test Data Document:
82577-3567353-1 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
16 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A458a0